

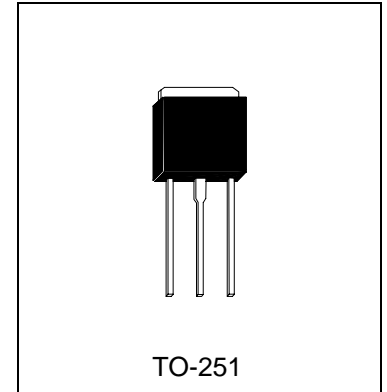


HI10387

NPN EPITAXIAL PLANAR TRANSISTOR

Description

The HI10387 is designed for general-purpose amplifier and low-speed switching applications.



Absolute Maximum Ratings (T_A=25°C)

- Maximum Temperatures
 - Storage Temperature -55~+150 °C
 - Junction Temperature 150°C Maximum
- Maximum Power Dissipation
 - Total Power Dissipation (T_C=25°C) 65 W
 - Total Power Dissipation (T_A=25°C) 2 W
- Maximum Voltages and Currents (T_A=25°C)
 - V_{CBO} Collector to Base Voltage 80 V
 - V_{CEO} Collector to Emitter Voltage 80 V
 - V_{EBO} Emitter to Base Voltage 5 V
 - I_C Collector Current 10 A

Electrical Characteristics (T_A=25°C)

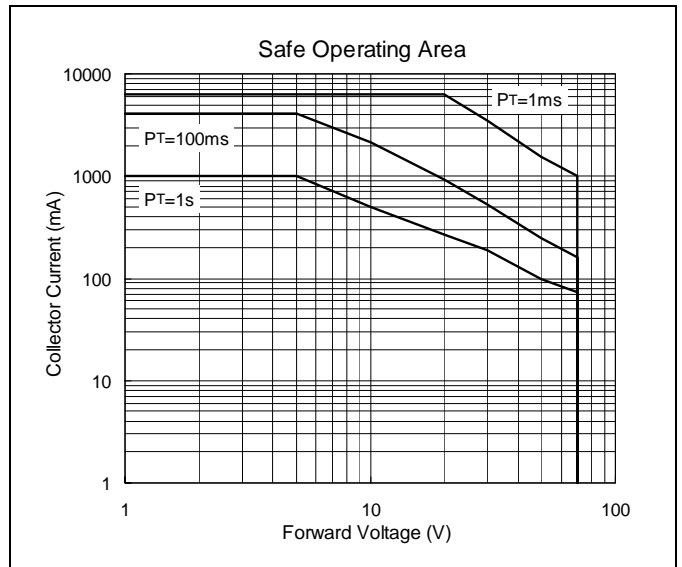
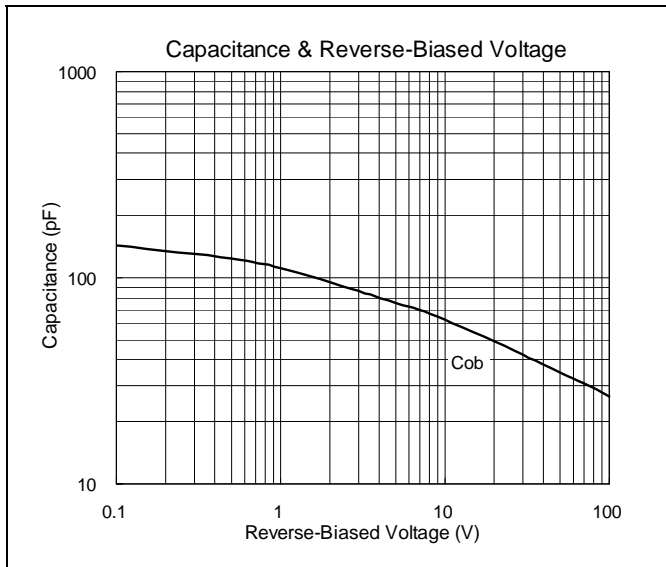
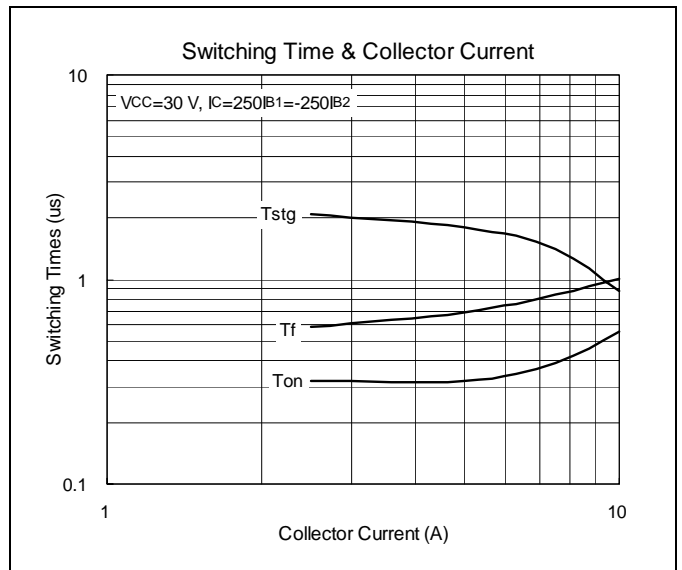
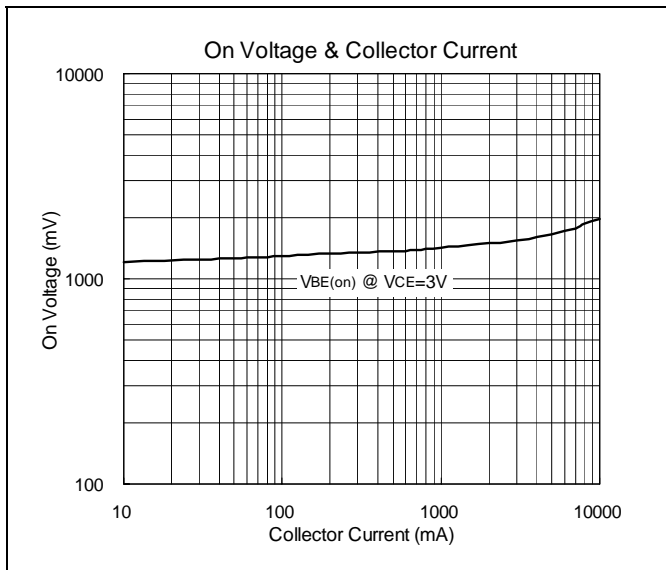
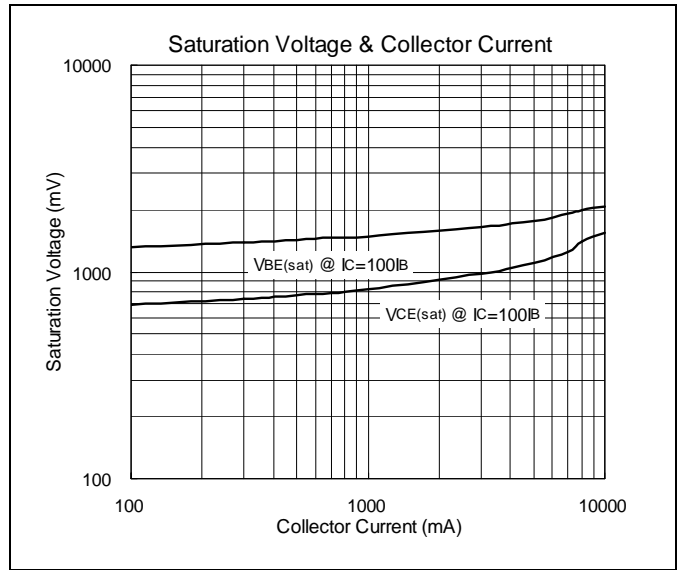
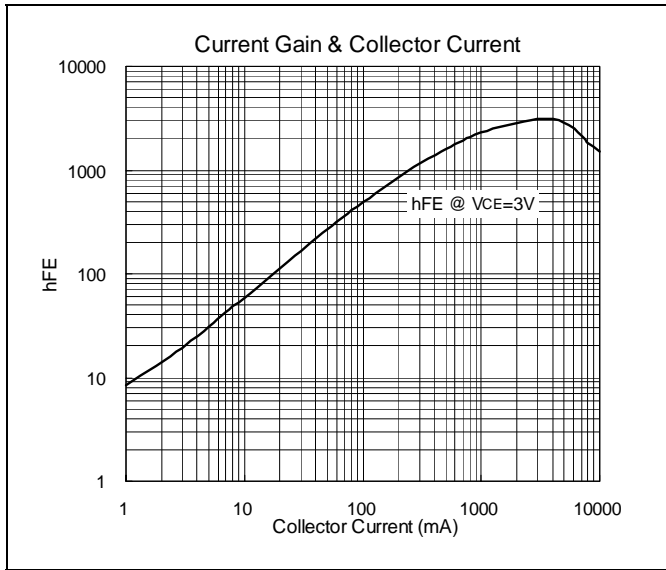
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CEO}	80	-	-	V	I _C =200mA
I _{CBO}	-	-	100	uA	V _{CB} =160V
I _{EBO}	-	-	2	mA	V _{EB} =5V
I _{CEO}	-	-	1	mA	V _{CE} =80V
I _{CEV}	-	-	300	uA	V _{CE} =80V, V _{BE(Off)} =1.5V
V _{CE(sat)1}	-	-	2	V	I _C =5A, I _B =10mA
V _{CE(sat)2}	-	-	3	V	I _C =10A, I _B =100mA
V _{CE(sat)3}	-	-	1.5	V	I _C =5A, I _B =2.5mA
V _{BE(sat)}	-	-	2	V	I _C =5A, I _B =5mA
V _{BE(on)1}	-	-	2.8	V	V _{CE} =3V, I _C =5A
V _{BE(on)2}	-	-	4.5	V	V _{CE} =3V, I _C =10A
V _{FEC}	-	-	3	V	I _C =5A
h _{FE1}	2	-	20	K	I _C =5A, V _{CE} =3V
h _{FE2}	100	-	-		V _{CE} =3V, I _C =10A

Classification Of V_{CE(sat)1}

Rank	KA	KB	KC	NORMAL
V _{CE(sat)1}	<1.5, BV _{CEO} >130V	<1.1V	<1.3V	<2V



Characteristics Curve





TO-251 Dimension

DIM	Min.	Max.
A	6.35	6.80
C	4.80	5.50
F	1.30	1.70
G	5.40	6.25
H1	6.75	8.00
K	0.50	0.90
K1	0.40	0.90
L	0.90	1.50
M	2.20	2.40
a1	0.40	0.65
a2	-	*2.30

*: Typical, Unit: mm

DIM	Min.	Max.
A	6.40	6.80
B	-	6.00
C	5.04	5.64
D	-	*4.34
E	0.40	0.80
F	0.50	0.90
G	5.90	6.30
H	-	*1.80
H1	-	*9.30
I	-	*16.10
J	-	*0.80
K	-	0.96
K1	-	*0.76
M	2.20	2.40
a1	0.40	0.60
a2	2.10	2.50
y1	-	5°
y2	-	3°

*: Typical, Unit: mm

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Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T_{Smin})	100°C	150°C
- Temperature Max (T_{Smax})	150°C	200°C
- Time (min to max) (t_s)	60~120 sec	60~180 sec
T_{Smax} to T_L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T_L)	183°C	217°C
- Time (t_L)	60~150 sec	60~150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec